SKKT 106, SKKT 106B, SKKH 106

SEMIPACK® 1

Thyristor / Diode Modules

SKKT 106

SKKT 106B

SKKH 106

Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

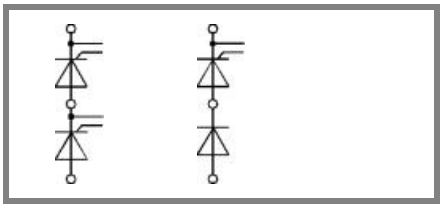
Typical Applications

- DC motor control (e. g. for machine tools)
- AC motor soft starters
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

V_{RSM} V	V_{RRM}, V_{DRM} V	I_{TRMS} = 180 A (maximum value for continuous operation) I_{TAV} = 106 A (sin. 180; T_c = 85 °C)		
900	800	SKKT 106/08E	SKKT 106B08E	SKKH 106/08E
1300	1200	SKKT 106/12E	SKKT 106B12E	SKKH 106/12E
1500	1400	SKKT 106/14E	SKKT 106B14E	SKKH 106/14E
1700	1600	SKKT 106/16E	SKKT 106B16E	SKKH 106/16E
1900	1800	SKKT 106/18E	SKKT 106B18E	SKKH 106/18E

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; T_c = 85 (100) °C;	106 (78)	A
I_D	P3/180F; T_a = 35 °C; B2 / B6	145 / 180	A
	P16/200F; T_a = 35 °C; B2 / B6	190 /260	A
I_{RMS}	P3/180F; T_a = 35 °C; W1 / W3	200 / 3 * 140	A
I_{TSM}	T_{vj} = 25 °C; 10 ms	2250	A
	T_{vj} = 130 °C; 10 ms	1900	A
i²t	T_{vj} = 25 °C; 8,3 ... 10 ms	25000	A²s
	T_{vj} = 130 °C; 8,3 ... 10 ms	18000	A²s
V_T	T_{vj} = 25 °C; I_T = 300 A	max. 1,65	V
$V_{T(TO)}$	T_{vj} = 130 °C	max. 0,9	V
r_T	T_{vj} = 130 °C	max. 2	mΩ
I_{DD}; I_{RD}	T_{vj} = 130 °C; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}	max. 20	mA
t_{gd}	T_{vj} = 25 °C; I_G = 1 A; di_G/dt = 1 A/µs	1	µs
t_{gr}	V_D = 0,67 * V_{DRM}	2	µs
$(di/dt)_{cr}$	T_{vj} = 130 °C	max. 150	A/µs
$(dv/dt)_{cr}$	T_{vj} = 130 °C	max. 1000	V/µs
t_q	T_{vj} = 130 °C	100	µs
I_H	T_{vj} = 25 °C; typ. / max.	150 / 250	mA
I_L	T_{vj} = 25 °C; R_G = 33 Ω; typ. / max.	300 / 600	mA
V_{GT}	T_{vj} = 25 °C; d.c.	min. 3	V
I_{GT}	T_{vj} = 25 °C; d.c.	min. 150	mA
V_{GD}	T_{vj} = 130 °C; d.c.	max. 0,25	V
I_{GD}	T_{vj} = 130 °C; d.c.	max. 6	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,28 / 0,14	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,3 / 0,15	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,32 / 0,16	K/W
$R_{th(c-s)}$	per thyristor / per module	0,2 / 0,1	K/W
T_{vj}		- 40 ... + 130	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15 %[1)]	Nm
M_t	to terminal	3 ± 15 %	Nm
a		5 * 9,81	m/s²
m	approx.	95	g
Case	SKKT	A 46	
	SKKT ...B	A 48	
	SKKH	A 47	



SKKT SKKH

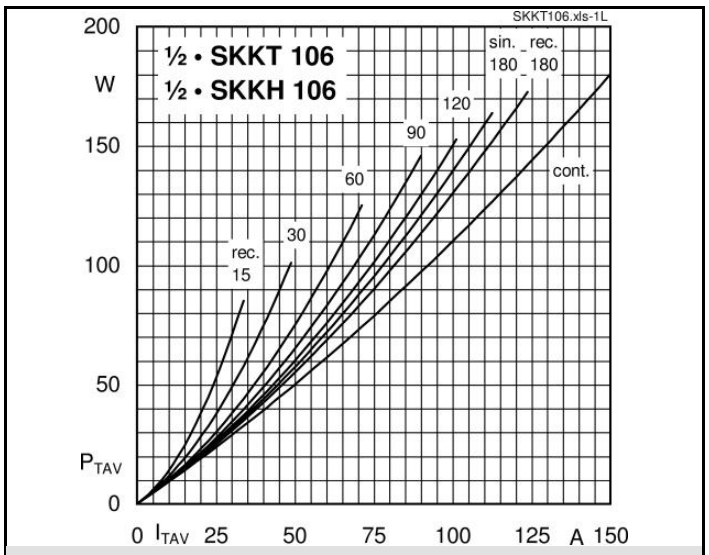


Fig. 1L Power dissipation per thyristor vs. on-state current

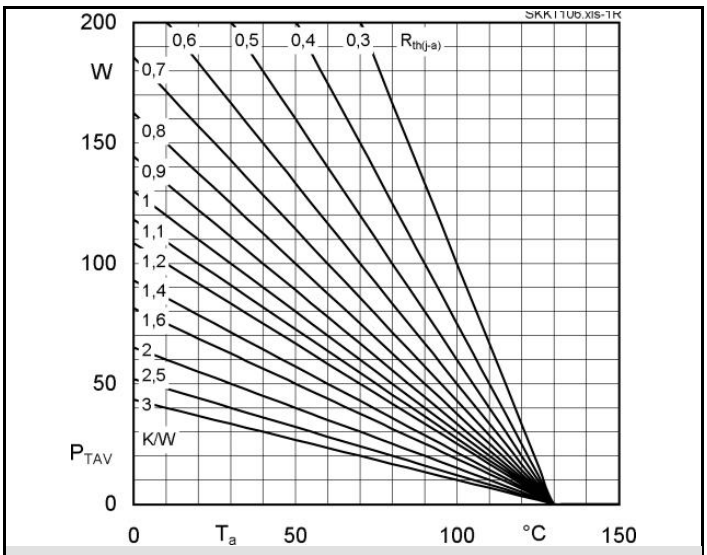


Fig. 1R Power dissipation per thyristor vs. ambient temp.

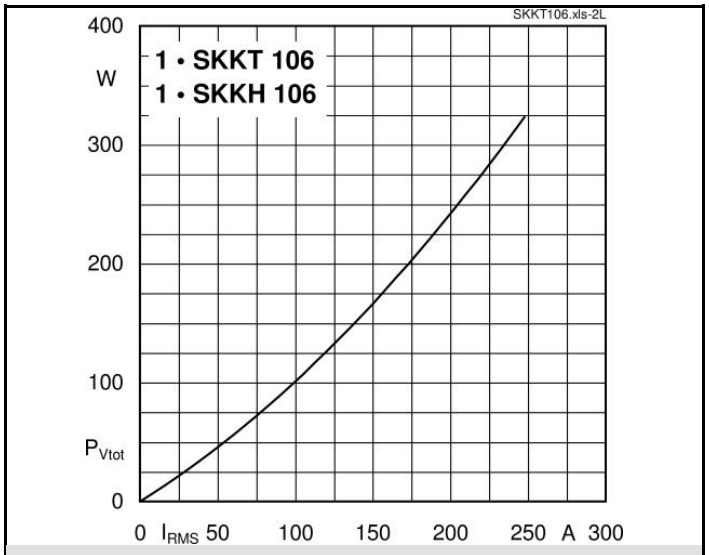


Fig. 2L Power dissipation per module vs. rms current

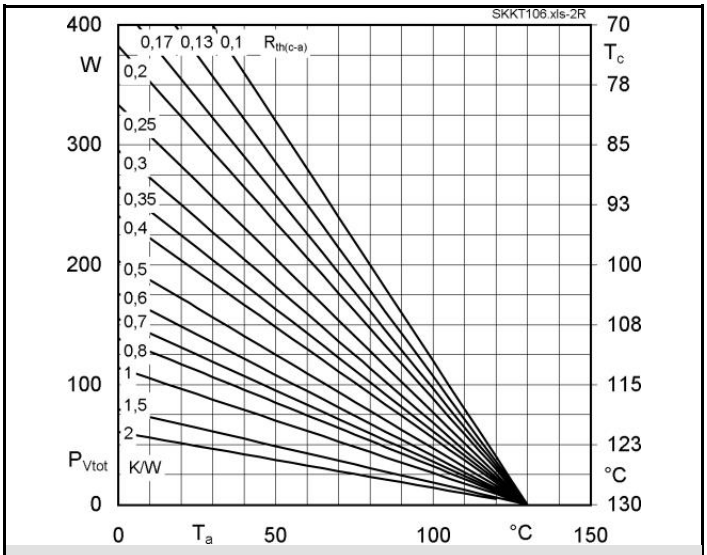


Fig. 2R Power dissipation per module vs. case temp.

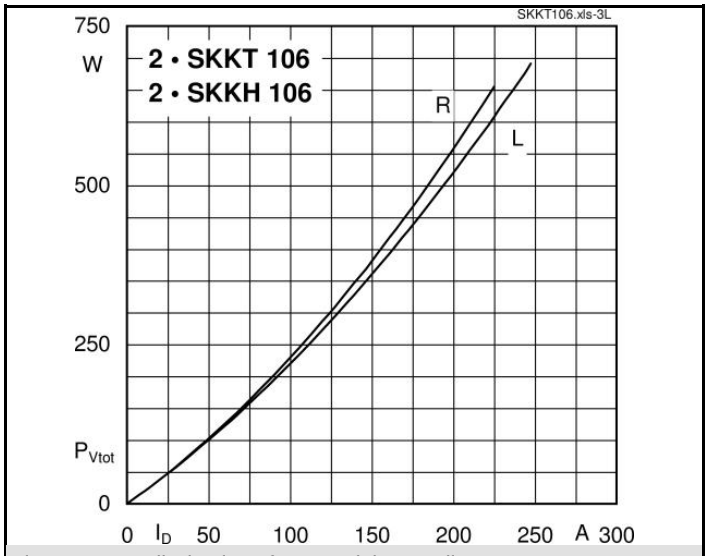


Fig. 3L Power dissipation of two modules vs. direct current

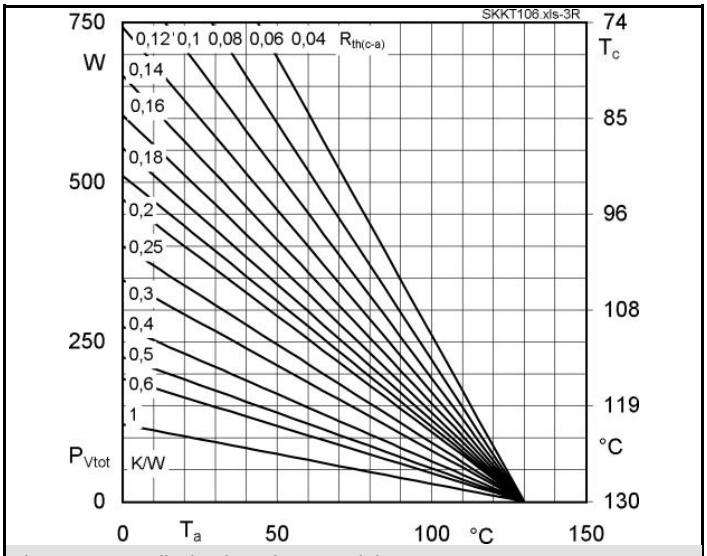


Fig. 3R Power dissipation of two modules vs. case temp.

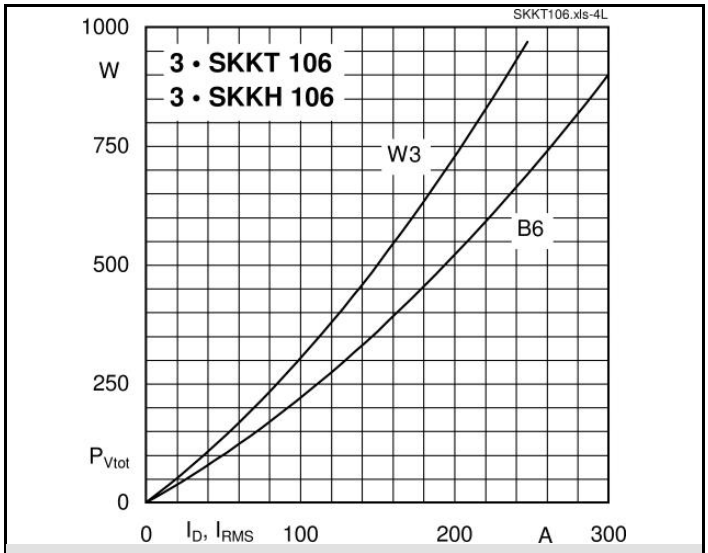


Fig. 4L Power dissipation of three modules vs. direct and rms current

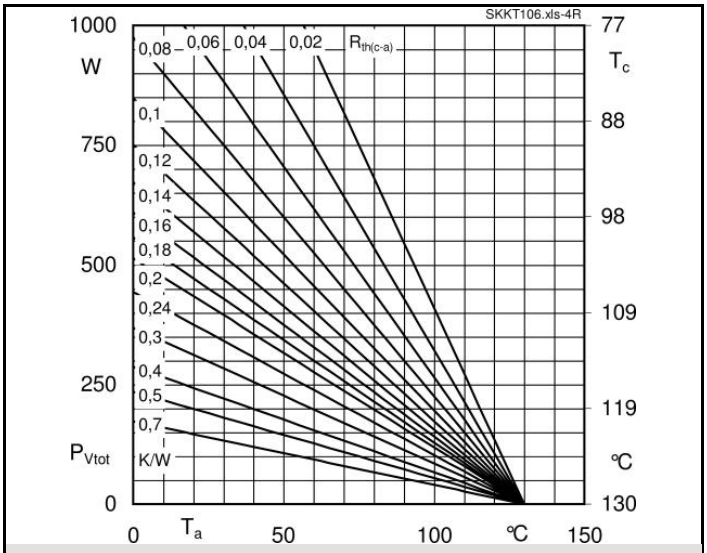


Fig. 4R Power dissipation of three modules vs. case temp.

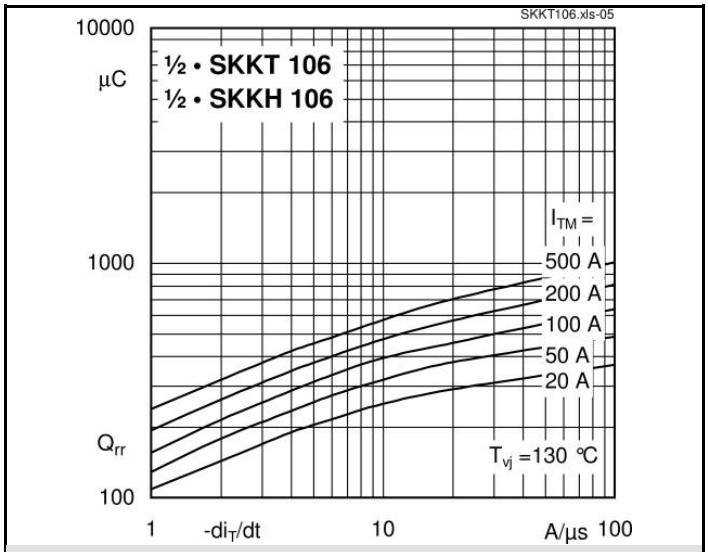


Fig. 5 Recovered charge vs. current decrease

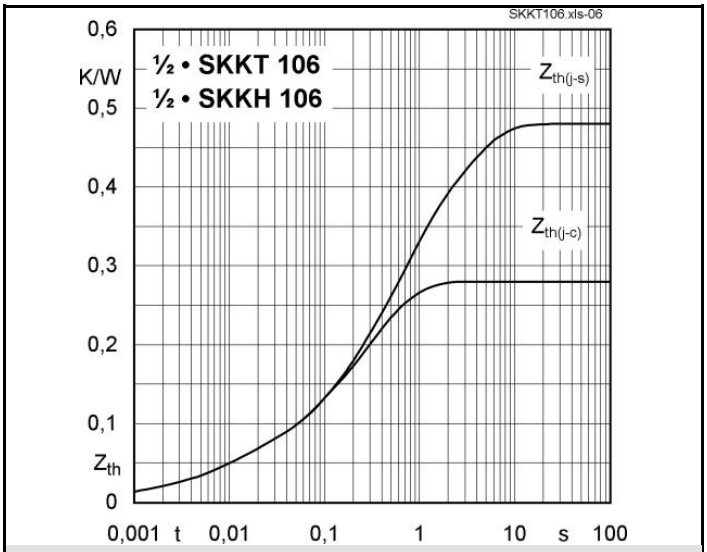


Fig. 6 Transient thermal impedance vs. time

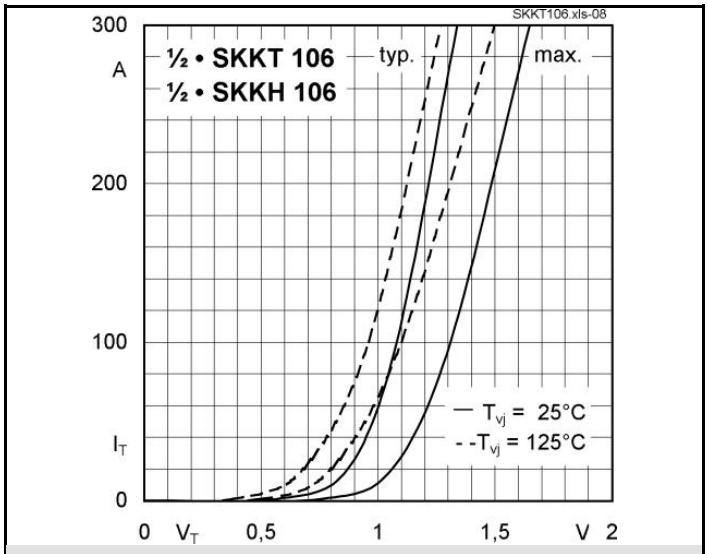


Fig. 7 On-state characteristics

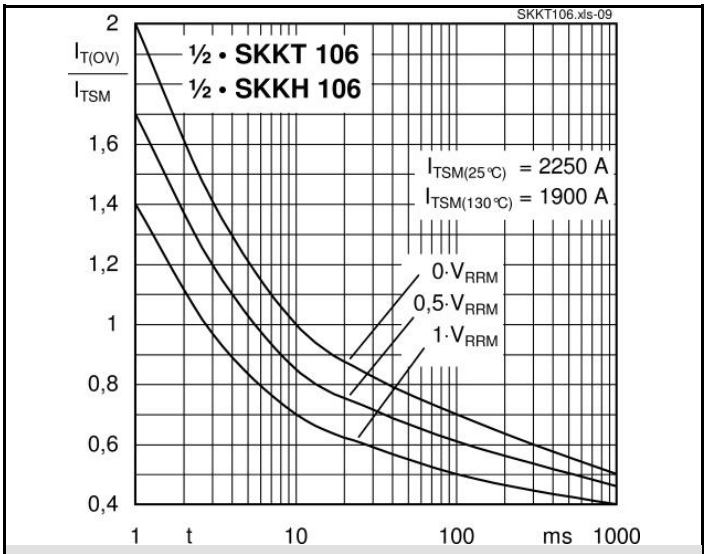


Fig. 8 Surge overload current vs. time

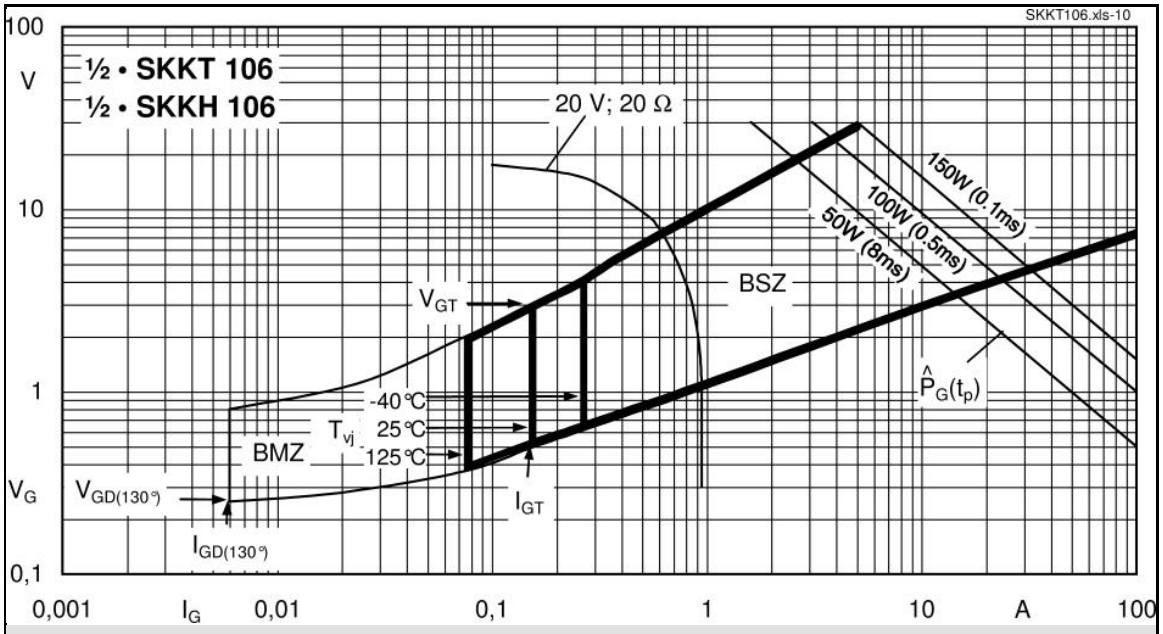
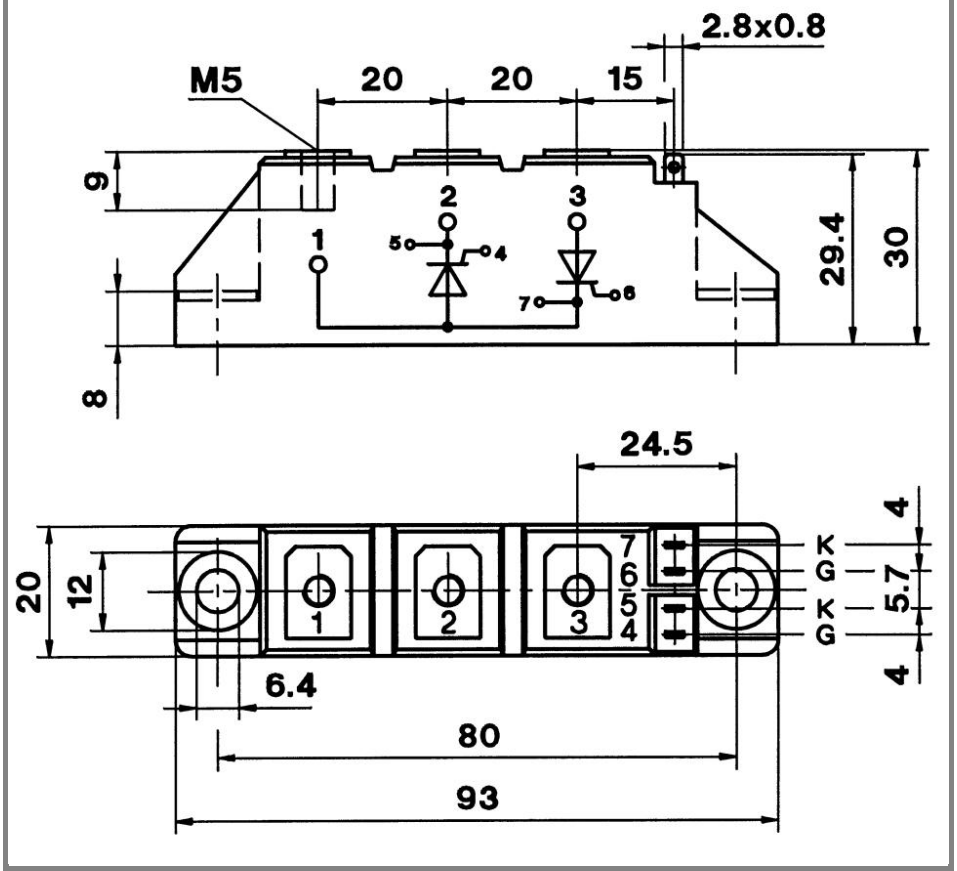
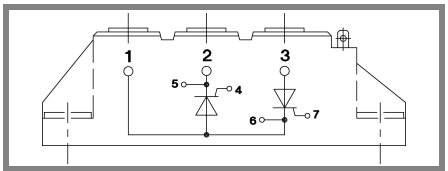


Fig. 9 Gate trigger characteristics

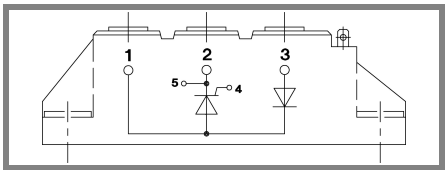
Dimensions in mm



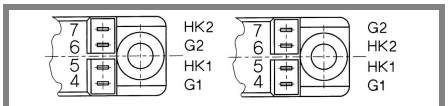
Case A 46 (SKKT)



Case A 48 SKKT ...B



Case A 47 SKKH



SKKT SKKT ...B

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